

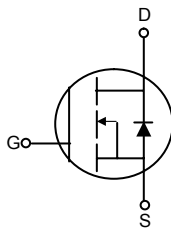
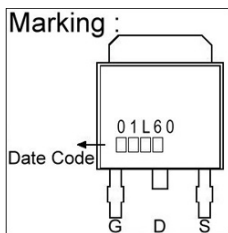
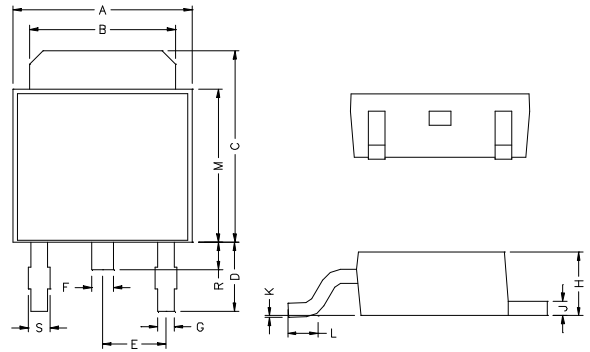
Description

The SSD01L60 (TO-252) is universally preferred for all commercial-industrial surface mount applications and suited for AC/DC converters.

Features

- * RoHs Compliant
- * Simple Drive Requirement
- * Fast Switching Speed
- * Repetitive Avalanche Rated

TO-252



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.20	2.80	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	±30	V
Continuous Drain Current, V _{GS} @10V	I _D @T _C =25°C	1	A
Continuous Drain Current, V _{GS} @10V	I _D @T _C =100°C	0.8	A
Pulsed Drain Current ¹	I _{DM}	3	A
Total Power Dissipation	P _D @T _C =25°C	29	W
Linear Derating Factor		0.232	W/°C
Single Pulse Avalanche Energy ²	E _{AS}	0.5	mJ
Avalanche Current	I _{AR}	1	A
Repetitive Avalanche Energy	E _{AR}	0.5	mJ
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-case	R _{thj-c}	4.3	°C/W
Thermal Resistance Junction-ambient	R _{thj-a}	110	°C/W

Electrical Characteristics(T_j=25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV _{DSS}	600	–	–	V	V _{GS} =0V, I _D =250μA
Breakdown Voltage Temp. Coefficient	ΔBV _{DSS} /ΔT _j	–	0.8	–	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	2.0	–	4.0	V	V _{DS} =V _{GS} , I _D =250μA
Gate-Source Leakage Current	I _{GSS}	–	–	±100	nA	V _{GS} =±30V
Drain-Source Leakage Current (T _j =25°C)	I _{DSS}	–	–	10	μA	V _{DS} =600V, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		–	–	100	μA	V _{DS} =480V, V _{GS} =0
Static Drain-Source On-Resistance ³	R _{DS(ON)}	–	–	12	Ω	V _{GS} =10V, I _D =0.5A
Forward Transconductance	G _{fs}	–	0.8	–	S	V _{DS} =10V, I _D =0.5A
Total Gate Charge ³	Q _g	–	4	–	nC	I _D =1 A V _{DS} =480V V _{GS} = 10V
Gate-Source Charge	Q _{gs}	–	1	–		
Gate-Drain ("Miller") Charge	Q _{gd}	–	1.1	–		
Turn-on Delay Time ³	T _{d(ON)}	–	6.6	–	nS	V _{DD} =300V I _D =1 A V _{GS} =10V R _G =3.3Ω R _D =300 Ω
Rise Time	T _r	–	5	–		
Turn-off Delay Time	T _{d(off)}	–	11.7	–		
Fall Time	T _f	–	9.2	–		
Input Capacitance	C _{iss}	–	170	–	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	–	30.7	–		
Reverse Transfer Capacitance	C _{rss}	–	5.1	–		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage ³	V _{SD}	–	–	1.2	V	I _S =1A, V _{GS} =0V, T _j =25°C
Continuous Source Current(Body Diode)	I _S	–	–	1	A	V _D =V _G =0V, V _S =1.2 V
Pulsed Source Current(Body Diode) ¹	I _{SM}	–	–	5	A	

Notes: 1. Pulse width limited by safe operating area.

2. Starting T_j=25°C, V_{DD}=50V, L=10mH, R_G=25Ω, I_{AS}=1.0A.

3. Pulse width ≤ 300us, duty cycle ≤ 2%.

Characteristics Curve

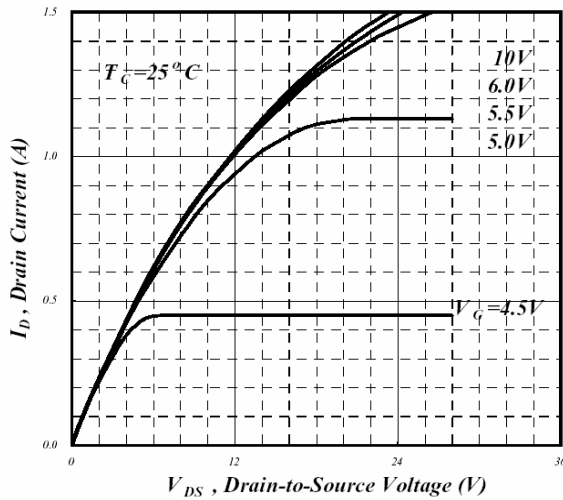


Fig 1. Typical Output Characteristics

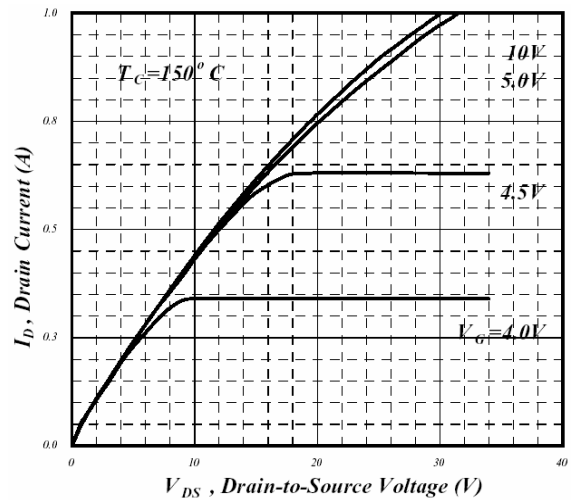


Fig 2. Typical Output Characteristics

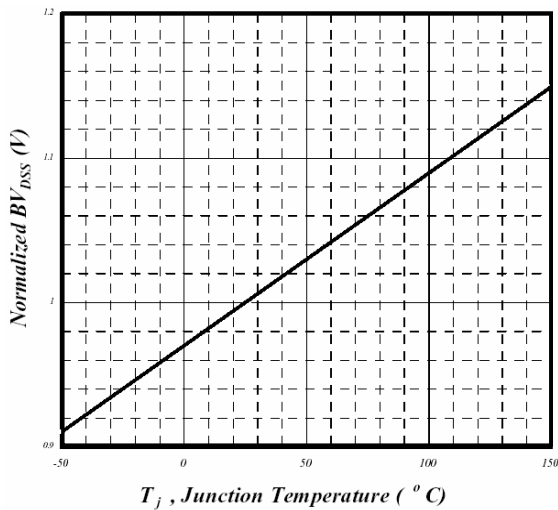


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

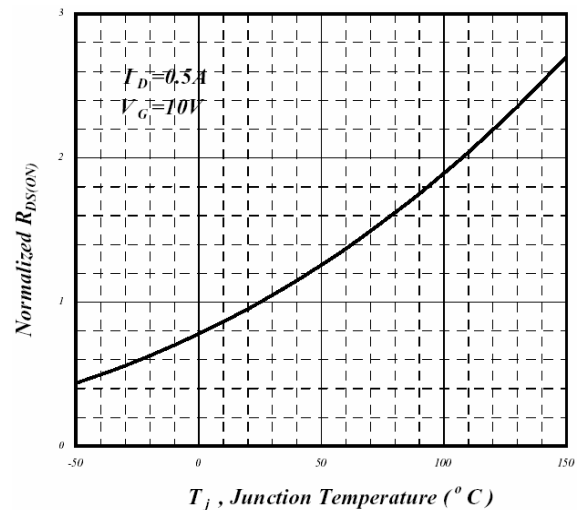


Fig 4. Normalized On-Resistance v.s. Junction Temperature

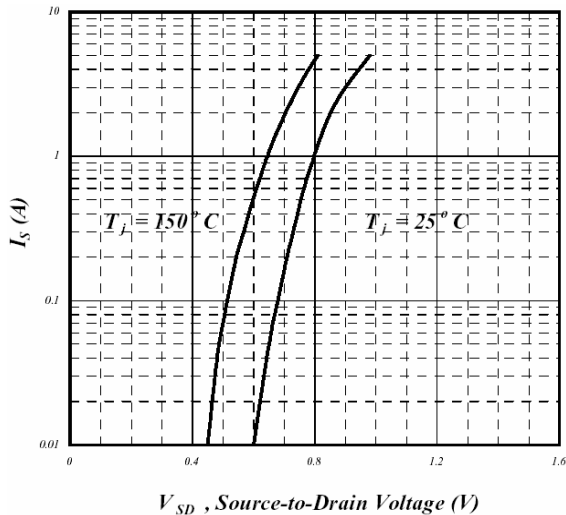


Fig 5. Forward Characteristics of Reverse Diode

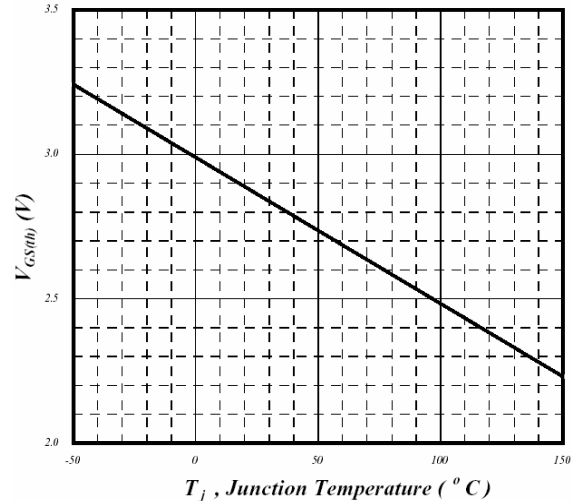


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

Any changing of specification will not be informed individual

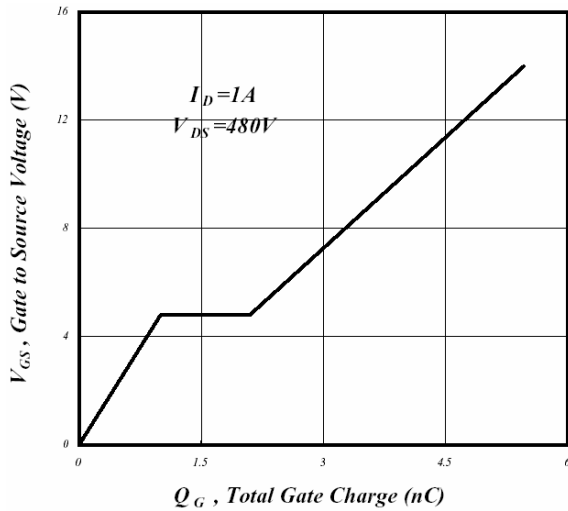


Fig 7. Gate Charge Characteristics

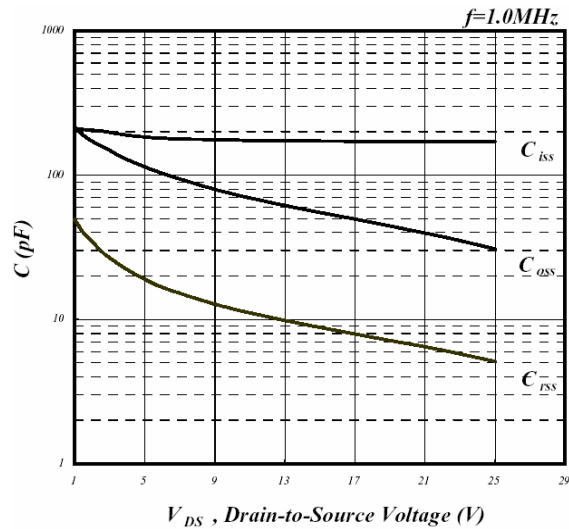


Fig 8. Typical Capacitance Characteristics

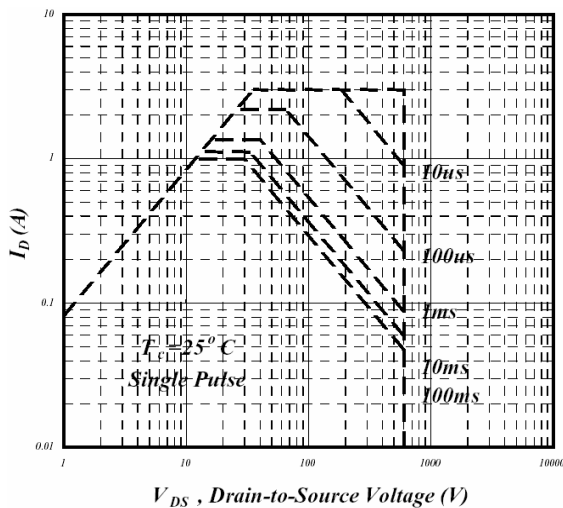


Fig 9. Maximum Safe Operating Area

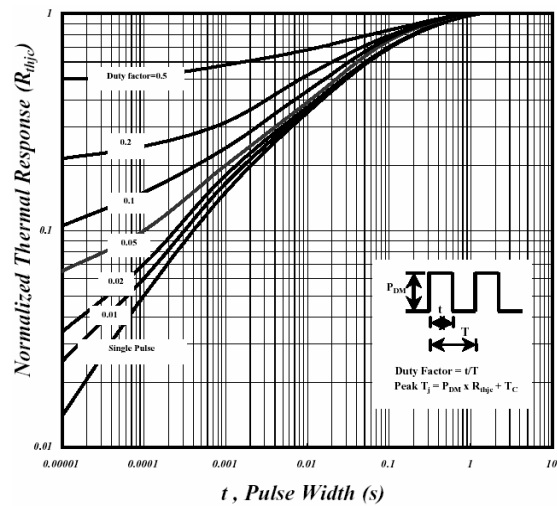


Fig 10. Effective Transient Thermal Impedance

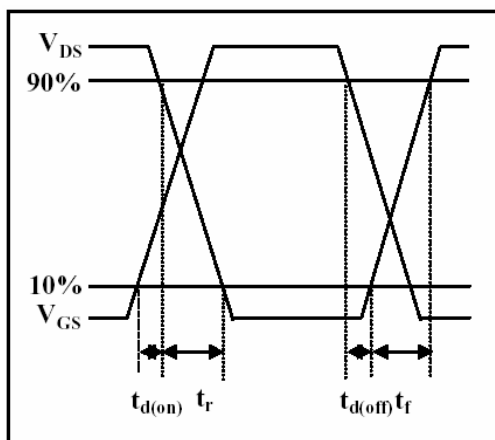


Fig 11. Switching Time Waveform

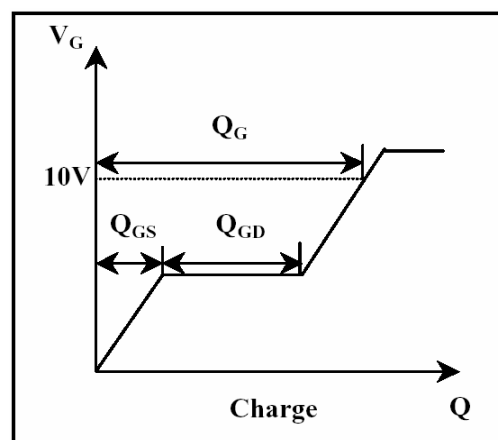


Fig 12. Gate Charge Waveform